

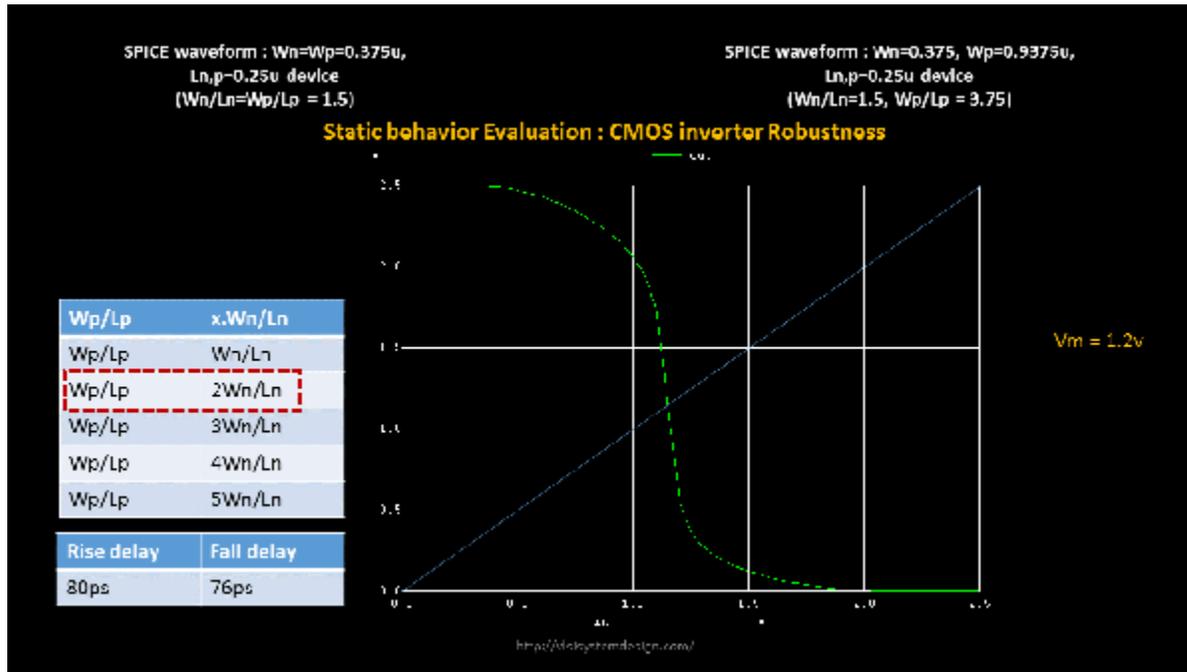


Switching threshold – Clock buffer

Kunal Ghosh

CMOS Logic so robust... I can give you 4 instances of this

1) Vary PMOS width size to its maximum, keeping NMOS width constant and with couple of SPICE simulations, it reveals a minimal variation on ‘switching threshold (V_m)’, while the functionality remains intact. Below 2 images has some SPICE simulations and numbers from experiments, I performed in my course “Circuit Design & SPICE simulations”



SPICE waveform : Wn=Wp=0.375u,
Ln,p=0.25u device
(Wn/Ln=Wp/Lp = 1.5)

SPICE waveform : Wn=0.375, Wp=0.9375u,
Ln,p=0.25u device
(Wn/Ln=1.5, Wp/Lp = 3.75)

Static behavior Evaluation : CMOS inverter Robustness
1. Switching Threshold, Vm

Wp/Lp	x.Wn/Ln	Rise delay	Fall delay	Vm
Wp/Lp	Wn/Ln	148ps	71ps	0.99v
Wp/Lp	2Wn/Ln	80ps	76ps	1.2v
Wp/Lp	3Wn/Ln	57ps	80ps	1.25v
Wp/Lp	4Wn/Ln	45ps	84ps	1.35v
Wp/Lp	5Wn/Ln	37ps	88ps	1.4v

Approximately equal rise-fall delay
Typical characteristics for a clock
inverter/buffer

Vm is the point where Vin = Vout

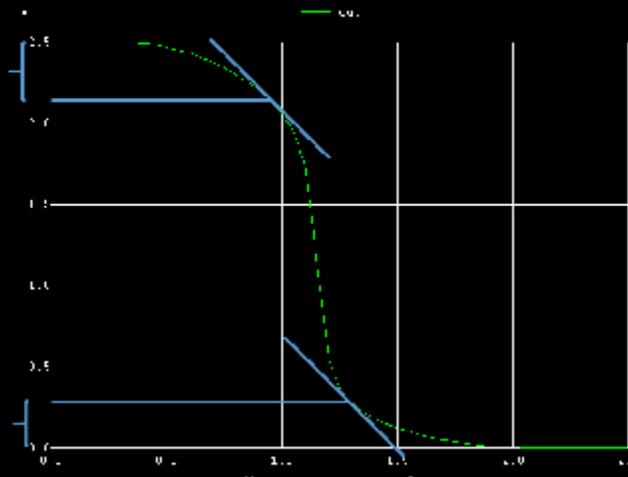
<http://vlsisystemdesign.com/>

2) Vary PMOS width size to its maximum, keeping NMOS width constant and with couple of SPICE simulations, it's also revealed that 'noise margin' has hardly any variation, while functionality remains intact. Watch!!!

Static behavior Evaluation : CMOS inverter Robustness
2. Noise Margin, NM_H and NM_L

Wp/Lp	x.Wn/Ln
Wp/Lp	Wn/Ln
Wp/Lp	2Wn/Ln
Wp/Lp	3Wn/Ln
Wp/Lp	4Wn/Ln
Wp/Lp	5Wn/Ln

NM _H	NM _L
0.35	0.3



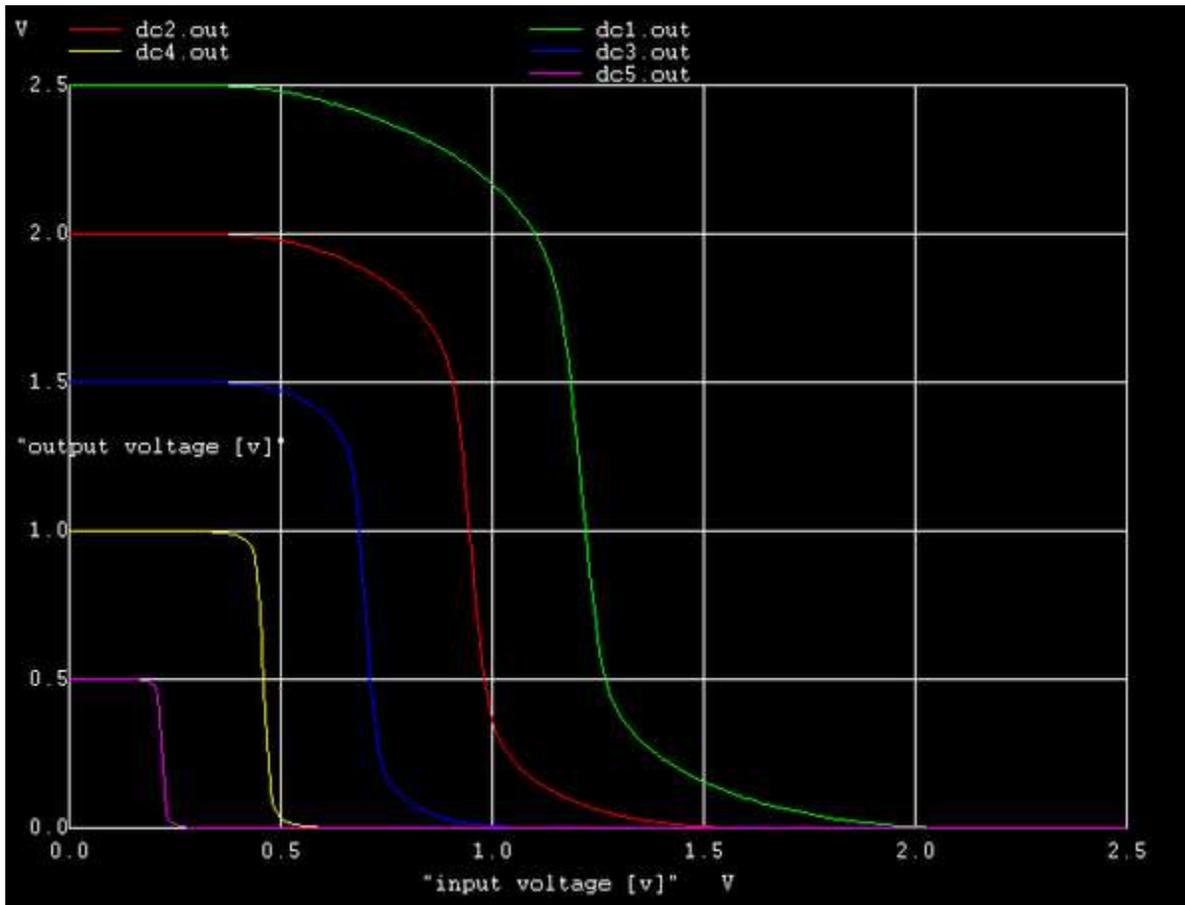
<http://vlsisystemdesign.com/>

Static behavior Evaluation : CMOS inverter Robustness
2. Noise Margin, NM_H and NM_L

W_p/L_p	$\times W_n/L_n$	NM_H	NM_L	V_m
W_p/L_p	W_n/L_n	0.3	0.3	0.59v
W_p/L_p	$2W_n/L_n$	0.35	0.3	1.2v
W_p/L_p	$3W_n/L_n$	0.4	0.3	1.25v
W_p/L_p	$4W_n/L_n$	0.42	0.27	1.35v
W_p/L_p	$5W_n/L_n$	0.42	0.27	1.4v

<http://www.vlsi-system-design.com/>

3) Vary power supply voltage (in full range, from slightly above threshold voltage till full supply VDD), keeping NMOS/PMOS width constant, the gain improves, while functionality is still intact. Watch!!

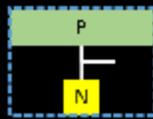


4) Now, vary, PMOS width from **Max to Min**, while vary NMOS width from **Min to Max** at same time, and there is very little impact in ‘**switching threshold**’ and ‘**noise margin**’, while functionality is still intact. Watch!!

Static behavior Evaluation : CMOS inverter Robustness
4. Device Variation

SPICE Simulation

Strong PMOS – Weak NMOS



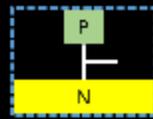
$W_p = 1.875u$

$W_n = 0.375u$

$W_p = 1.875u \rightarrow 0.375u$

$W_n = 0.375u \rightarrow 1.875u$

Weak PMOS – Strong NMOS

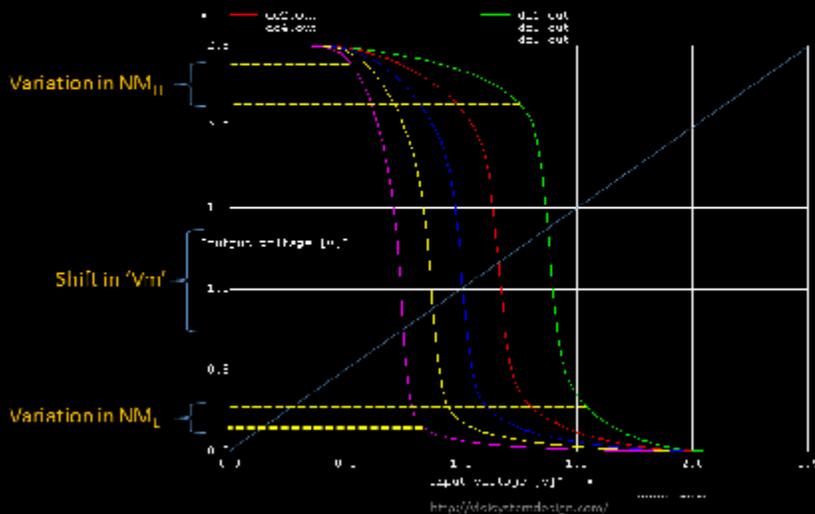


$W_p = 0.375u$

$W_n = 1.875u$

<http://MaksymenkoDesign.com/>

Static behavior Evaluation : CMOS inverter Robustness
4. Device Variation



<http://MaksymenkoDesign.com/>

“Remember, the storm is a good opportunity for the pine and the cypress to show their strength and stability” — Ho Chi Minh

So, what is that storm, that will cause a CMOS logic to become unstable – may be a ‘glitch’. I have given enough hint for you to figure out that. Well, that would one of the key topics of my next course, when I go for dynamic simulations.

And here’s more reason to be happy to discover what **defines a buffer/inverter as clock cell or regular cell.**

This is also, a common question that STA engineers have while hearing about **clock path full of clock buffers/inverters.** Well, let me try to begin to answer it over here

In last post, I talked about the robustness of CMOS logic in terms of switching threshold (i.e. a voltage at which $V_{in} = V_{out}$), and below table summarizes it all

SPICE waveform : Wn=Wp=0.375u,
Ln,p=0.25u device
(Wn/Ln=Wp/Lp = 1.5)

SPICE waveform : Wn=0.375, Wp=0.9375u,
Ln,p=0.25u device
(Wn/Ln=1.5, Wp/Lp = 3.75)

Static behavior Evaluation : CMOS inverter Robustness

1. Switching Threshold, V_m

$$V_m = R \cdot V_{dd} / (1+R)$$

$$\text{Where } R = \frac{K_p \cdot V_{dsatp}}{K_n \cdot V_{dsatn}} = \frac{\left(\frac{W_p}{L_p}\right) K_{pp} \cdot V_{dsatp}}{\left(\frac{W_n}{L_n}\right) K_{nn} \cdot V_{dsatn}}$$

$$\left(\frac{W_p}{L_p}\right) = \frac{K_{nn} \cdot V_{dsatn} [(V_{in} - V_t)] - \frac{V_{dsatn}}{2}}{K_{pp} \cdot V_{dsatp} [-V_m + V_{dd} + V_t] + \frac{V_{dsatp}}{2}}$$

V_m is the point where V_{in} = V_{out}

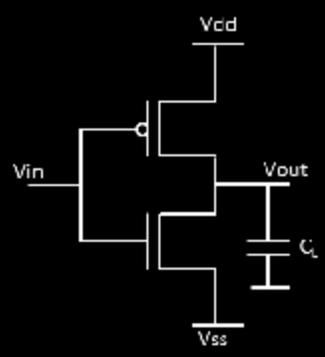
<http://dalyrj.com/design/conv/>

“On a side note” – it’s always possible to hand-calculate the value of switching threshold, if you know the sizes of transistors. Below image will give a straight forward equation to do that (if it looks complex, don’t worry, it has nothing to do with this post, you can safely scroll over :))

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(Wn/Ln=1.5, Wp/Lp = 3.75)

Static behavior Evaluation : CMOS inverter Robustness
1. Switching Threshold, Vm



$$I_{dsP} = -I_{dsN}$$

$$I_{dsP} + I_{dsN} = 0$$

$$k_p \cdot \left[\left((V_m - V_{dd} - V_t) \cdot V_{dsatp} \right) - \frac{V_{dsatp}^2}{2} \right] + k_n \cdot \left[\left((V_m - V_t) \cdot V_{dsatn} \right) - \frac{V_{dsatn}^2}{2} \right] = 0$$

Solving the above for Vm

$$V_m = R \cdot V_{dd} / (1+R)$$

$$\text{Where } R = \frac{K_p \cdot V_{dsatp}}{K_n \cdot V_{dsatn}} = \frac{\left(\frac{W_p}{L_p}\right) K_{p\mu} \cdot V_{dsatp}}{\left(\frac{W_n}{L_n}\right) K_{n\mu} \cdot V_{dsatn}}$$

Vm ~ 0.98v

Vm is the point where Vin = Vout

Vm ~ 1.2v

<http://daskyramdesign.com/>

Alternatively, if you want to **design your CMOS inverter around certain switching threshold**, you can do that as well. Below equation will help to obtain the same (Again, if you do not follow this equation, just scroll over:), you can always learn about it in my [Circuit design course](#))

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Static behavior Evaluation : CMOS inverter Robustness
1. Switching Threshold, Vm

$$V_m = R \cdot V_{dd} / (1+R)$$

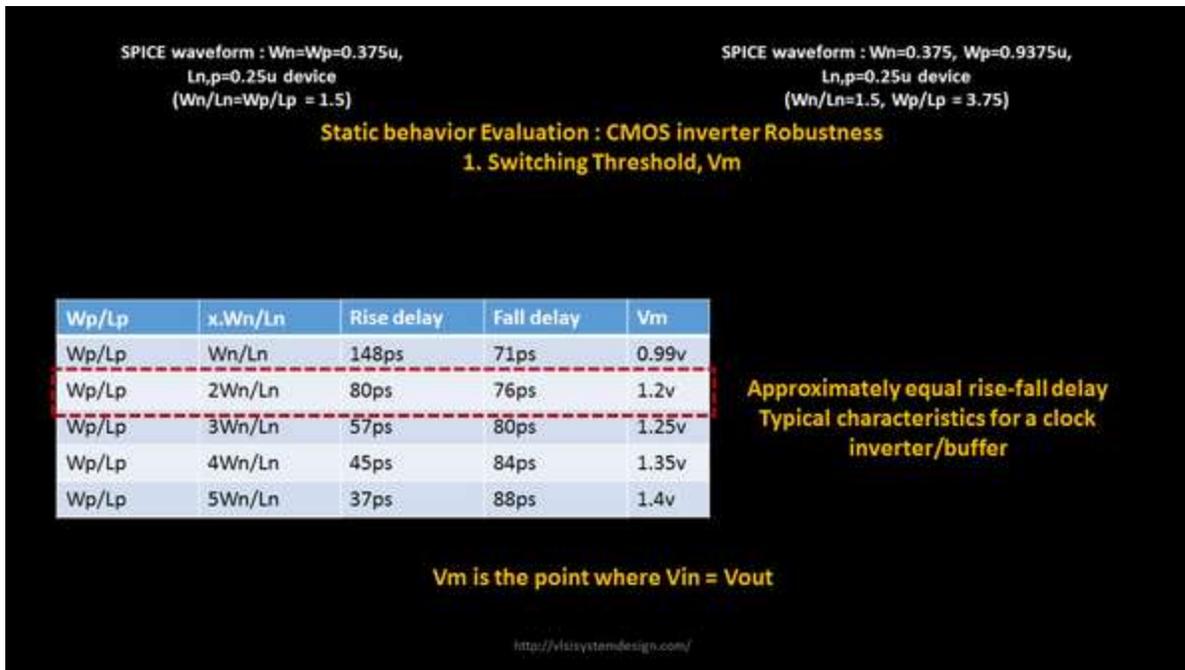
$$\text{Where } R = \frac{K_p \cdot V_{dsatp}}{K_n \cdot V_{dsatn}} = \frac{\left(\frac{W_p}{L_p}\right) K_{p\mu} \cdot V_{dsatp}}{\left(\frac{W_n}{L_n}\right) K_{n\mu} \cdot V_{dsatn}}$$

$$\left(\frac{W_p}{L_p}\right) \frac{K_{p\mu}}{K_{n\mu}} = \frac{k_{n\mu} \cdot v_{dsatn} \left[(V_m - V_t) - \frac{v_{dsatn}}{2} \right]}{K_p \cdot v_{dsatp} \left[(-V_m + V_{dd} + V_t) + \frac{v_{dsatp}}{2} \right]}$$

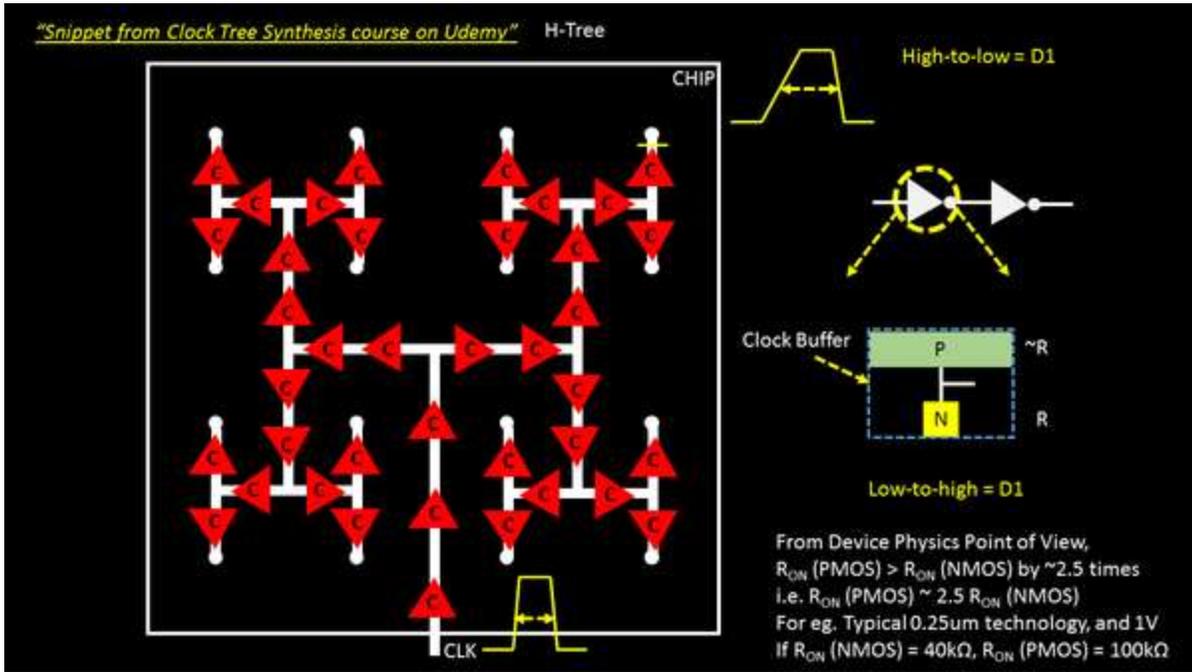
Vm is the point where Vin = Vout

<http://daskyramdesign.com/>

Moving on ... If you observe the below table, you will find out, that **if PMOS is twice the NMOS in a CMOS inverter**, you get the switching threshold close to middle of your supply voltage, and you also get a **benefit of equal rise-fall time of that inverter**. Same logic applies for buffer as well



If you recollect the below image from my [clock tree synthesis course](#), where the clock signal from clock port got disturbed at flop clock pin



I had solved this problem using a clock cell, whose rise-fall delay was exactly (or approximately) the same

